

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Selzer
 Application No.: 09/876,443
 Filing Date: June 7, 2001
 Title: Method of Improving X-Ray
 Lithography in the Sub 100nm
 Range to Create High Quality
 Semiconductor Devices

Docket No. 1520-006 (1426)
 Date: May 8, 2002
 Group Art Unit: 2882
 Examiner: I. Kiknadze
 FAX: 703 305-3594
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JUN 14 2002

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Terminal Disclaimer Under 37 CFR 1.321(c)

✓ Applicant disclaims term of any patent granted on this application extending beyond the term of US Patent 6,295,332.

The present application is commonly assigned with US Patent 6,295,332.

A fee sheet and the fee set forth in 37 CFR 1.20(d) is attached.

Any patent granted on the application shall be enforceable only for and during such period that said patent is commonly owned with the patent which formed the basis for the double patenting rejection (US Patent 6,295,332).

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Respectfully submitted,
 For: Selzer et al.

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